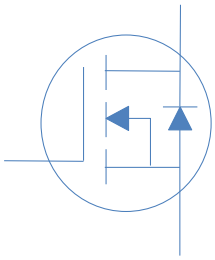
			Ω
			Ω



	Package	Marking

=25 (unless otherwise specified)

		=25		
		=100		
Drain to Source Voltage				
Gate to Source Voltage				
Avalanche Energy, Single Pulse		=25		mJ
		=25		W
	J			

Thermal Resistance Junction-Case	ΘJC		/W
Thermal Resistance Junction-Ambient	ΘJA		/W

Electrical Characteristics at T =25 (unless otherwise specified)

Static Characteristics

Drain to Source Breakdown Voltage	(BR)DSS	μ				
		μ				
		=25				μ
		=100				
Gate to Source Leakage Current						
Drain to Source on Resistance						Ω
						Ω
Transconductance	fs					
Gate Resistance		Open, f=1MHz				Ω

Dynamic Characteristics

Input Capacitance		=125V, f=1MHz				
Output Capacitance						
Reverse Transfer Capacitance						
Gate to Source Charge						
		Ω				
Turn off Delay Time	d(off)					
	f					

Reverse Diode Characteristics

Reverse Recovery Time		/dt=100A/μ				
Reverse Recovery Charge						

Fig 1. Typical Output Characteristics	Figure 2. On-Resistance vs. Gate-Source Voltage

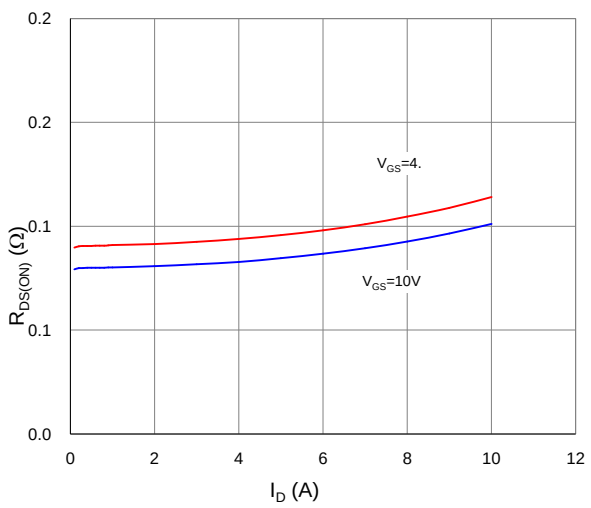
Figure 3. On-Resistance vs. Drain Current and Gate Voltage	Figure 4. Normalized On-Resistance vs. Junction Temperature
	

Figure 5. Typical Transfer Characteristics	Figure 6. Typical Source-Drain Diode Forward Voltage

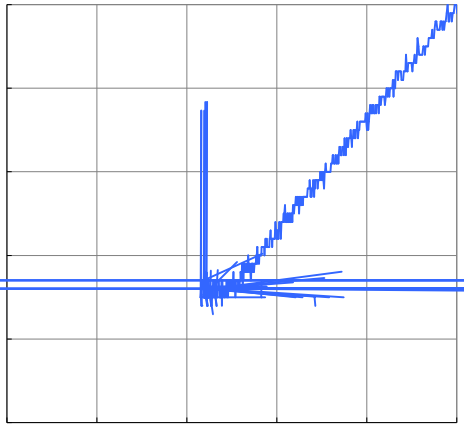
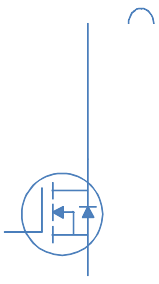
Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage	Figure 8. Typical Capacitance vs. Drain-to-Source Voltage
	

Figure 9. Maximum Safe Operating Area	

Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case

Inductive switching Test	

Uclamped Inductive Switching (UIS) Test	
	

Diode Recovery Test	